

isc N-Channel MOSFET Transistor

FCPF850N80Z

FEATURES

- Drain Current : I_D= 8A@ T_C=25 $^\circ\!\!\mathbb{C}$
- Drain Source Voltage
 : V_{DSS}= 800V(Min)
- Static Drain-Source On-Resistance
 - : R_{DS(on)} = 0.85 Ω (Max) @ V_{GS}= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

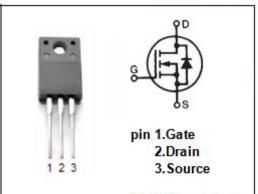
 motor drive, DC-DC converter, power switch and solenoid drive.

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

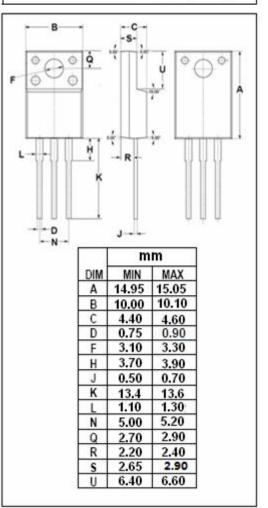
SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GSS}	Gate-Source Voltage	±20	V
ID	Drain Current-Continuous;@Tc=25℃	8	A
I _{DM}	Drain Current-Single Pulsed	18	A
PD	Total Dissipation	28	W
Tj	Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	4.4	°C/W







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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	800			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D = 0.6mA	2.5		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 3A			0.85	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±10	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V			25	uA
Vsd	Diode forward voltage	I _{SD} = 6A, V _{GS} = 0 V			1.2	V

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